Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	20	(US-4607530-$ or US-6594625-$ or US-6006026-$ or US-6684181-$ or US-6327555-$ or US-6285970-$ or US-6154718-$ or US-6154717-$ or US-6148276-$ or US-6144929-$ or US-6120548-$ or US-6041174-$ or US-5999719-$ or US-6581028-$ or US-5557710-$ or US-6242272-$ or US-6505147-$ or US-5889687-$ or US-5930494-$ or US-6080200-$). did.	USPAT	OR	OFF	2005/07/21 17:18
S1	252	semiconductor with (fab fabricat$4) with (simulat$4 model$4)	USPAT	OR	OFF	2005/07/20 13:11
S2	4	(fair adj model) or (fair adj diffusion adj model)	USPAT	OR	OFF	2005/07/20 13:11
S3	1	("6154717").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:24
S4	6	"10/989011" "10/780938" "10/668621" "09/891400" "09/781421" "09/519856"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:29
S5	1428	703/2.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:29
S6	146	S5 and (diffusion impurit$3 impure)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:31
S7	191	("pile-up" (pile adj up)) same (diffusion diffus$4)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:32
S8	1	10/059176	US-PGPUB	OR	OFF	2005/07/20 16:01
S10	1	"6581028".pn.	USPAT	OR	OFF	2005/07/20 17:15
S11	245	reverse adj short adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 17:15
S12	21	("5930494" "5819073" "5557710" "5684723" "6195790" "5148379" "6360190" "6242272" "6006026" "6080200" "5828586" "5889687" "6185472" "5819073" "6041424" "4584662" "6182270" "6011914" "6144932" "6360190" "6154717" "6505147" "6144929").pn.	USPAT	OR	OFF	2005/07/21 16:42

S13	13	("5103415" | "5671395" | "5675522" | "5677846" | "5774696" | "5784302" | "5819073" | "5828586" | "5889680" | "5930494" | "5963732" | "6006026" | "6011914").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/21 11:01
S14	19	(US-4607530-$ or US-6594625-$ or US-6006026-$ or US-6684181-$ or US-6327555-$ or US-6285970-$ or US-6154718-$ or US-6154717-$ or US-6148276-$ or US-6144929-$ or US-6120548-$ or US-6041174-$ or US-5999719-$ or US-6581028-$ or US-5557710-$ or US-6242272-$ or US-6505147-$ or US-5889687-$ or US-5930494-$).did.	USPAT	OR	OFF	2005/07/21 11:53
S15	1	S14 and (SiO)	USPAT	OR	OFF	2005/07/21 11:53
S16	9	S14 and layer	USPAT	OR	OFF	2005/07/21 12:05
S17	5	S14 and (source drain)	USPAT	OR	OFF	2005/07/21 12:10
S18	4	S17 and distance	USPAT	OR	OFF	2005/07/21 13:17
S19	1	"6080200".pn.	USPAT	OR	OFF	2005/07/21 13:11
S20	258	(impurity adj diffusion) same (source drain) same (distance length)	USPAT	OR	OFF	2005/07/21 13:23
S21	39	S20 and (simulat$4 model$4)	USPAT	OR	OFF	2005/07/21 13:18

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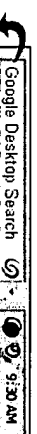
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